## **MAXIMUM RATINGS**

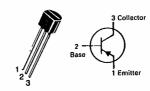
MAXIMON IN INCO				
Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	VCEO	25	Vdc	
Collector-Base Voltage	V <sub>CBO</sub>	25	Vdc	
Collector Current — Continuous	lc	600	mAdc	
Total Device Dissipation @ TA = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C	
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C	
Operating and Storage Junction	TJ, Tstg	-55 to +150	°C	

## THERMAL CHARACTERISTICS

HENNIAL CHARACTERISTICS				
Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction to Case	RejC	83.3	°C/W	
Thermal Resistance, Junction to Ambient(1)	R <sub>AJA</sub>	200	°C/W	

## MPSD55

CASE 29-04, STYLE 1 TO-92 (TO-226AA)



**AMPLIFIER TRANSISTOR** PNP SILICON

Refer to 2N4400 for MPSD05 graphs.\*

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				r
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mAdo, I <sub>B</sub> = 0)	V(BR)CEO	25	_	Vdc
Collector-Base Breakdown Voltage (tC = 10 μAdc, tE = 0)	V(BR)CBO	25		Vdc
Collector Cutoff Current (VCE = 20 Vdc)	ICEO	_	1.0	μAdc
Collector Cutoff Current (VCR = 20 Vdc, I <sub>E</sub> = 0)	ІСВО		1.0	μAdc
Emitter Cutoff Current (VEB = 3.0 Vdc, IC = 0)	lEBO .		100	nAdc
ON CHARACTERISTICS(2)			····	
DC Current Gain (IC = 50 mAdc, VCE = 5.0 Vdc) (IC = 100 mAdc, VCE = 5.0 Vdc) (IC = 500 mAdc, VCE = 5.0 Vdc)	hFE	50 80 30	=======================================	
Collector-Emitter Saturation Voltage (IC = 100 mAdc, IB = 10 mAdc)	V <sub>CE</sub> (sat)		0.5	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I <sub>C</sub> = 50 mAde, V <sub>CE</sub> = 10 Vdc, f = 100 MHz)	fr	100	_	MHz

<sup>(1)</sup> R<sub>BJA</sub> is measured with the device soldered into a typical printed circuit board. (2) Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.
\*Refer to 2N4402 for MPSD55 graphs.